ABSTRACT OF THE DISCLOSURE

An insulated gate transistor in which nitride oxide film having a nitrogen concentration of 1×10^{20} (/cm^3) or more and containing a halogen element is used as a gate insulator. Because the gate insulator has a nitrogen concentration of 1×10^{20} (/cm^3) or more, boron contained in the gate electrode of the p-type transistor is never diffused into the channel. Further because a halogen element is contained in the gate insulator, transistor conductance is increased and reliability in hot carrier injection is improved. Thus, an insulated gate transistor which has a sufficiently large conductance and which is superior in reliability can be fabricated.